

MMBD4148

High-speed switching diode Rev. 01 — 4 June 2009

Product data sheet

Product profile

1.1 General description

High-speed switching diode, encapsulated in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

1.2 Features

- High switching speed: $t_{rr} \le 4$ ns
- Low leakage current
- Repetitive peak reverse voltage: $V_{RRM} \le 75 \text{ V}$
- Low capacitance
- Reverse voltage: V_R ≤ 75 V
- Small SMD plastic package

1.3 Applications

- High-speed switching
- General-purpose switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{R}	reverse voltage		-	-	75	V
I _R	reverse current	V _R = 75 V	-	-	0.5	μΑ
t _{rr}	reverse recovery time		<u>[1]</u> -	-	4	ns

^[1] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.

Pinning information 2.

Table 2. **Pinning**

	3		
Pin	Description	Simplified outline	Graphic symbol
1	anode		
2	not connected		3
3	cathode	1 2	1



3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
MMBD4148	-	plastic surface-mounted package; 3 leads	SOT23		

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
MMBD4148	A6*

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	75	V
V_{R}	reverse voltage		-	75	V
I _F	forward current		<u>[1]</u> _	215	mA
I _{FRM}	repetitive peak forward current	$t_p \leq 0.5~\mu\text{s}; \\ \delta \leq 0.25$	-	500	mA
I _{FSM}	non-repetitive peak forward current	square wave	<u>[2]</u>		
		$t_p = 1 \mu s$	-	4	Α
		$t_p = 1 \text{ ms}$	-	1	Α
		$t_p = 1 s$	-	0.5	Α
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> _	250	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] $T_j = 25$ °C prior to surge.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] _	-	500	K/W
$R_{th(j-t)}$	thermal resistance from junction to tie-point		-	-	330	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

Table 7. Characteristics

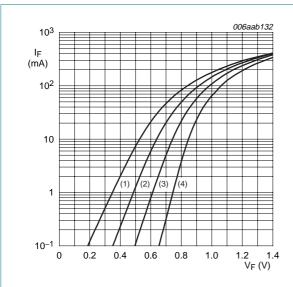
 T_{amb} = 25 °C unless otherwise specified.

	•					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage		<u>[1]</u>			
		$I_F = 1 \text{ mA}$	-	-	715	mV
		$I_F = 10 \text{ mA}$	-	-	855	mV
		$I_F = 50 \text{ mA}$	-	-	1	V
		I _F = 150 mA	-	-	1.25	V
I _R revers	reverse current	V _R = 25 V	-	-	30	nA
		V _R = 75 V	-	-	0.5	μΑ
		V _R = 25 V; T _j = 150 °C	-	-	30	μΑ
		V _R = 75 V; T _j = 150 °C	-	-	50	μΑ
C_{d}	diode capacitance	$f = 1 MHz; V_R = 0 V$	-	-	1.5	pF
t _{rr}	reverse recovery time		[2] _	-	4	ns
V_{FR}	forward recovery voltage		[3] _	-	1.75	V

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

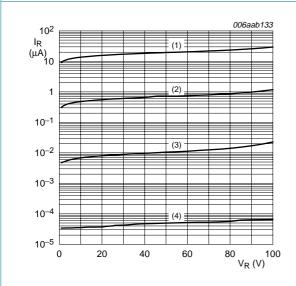
^[2] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.

^[3] When switched from $I_F = 10$ mA; $t_r = 20$ ns.



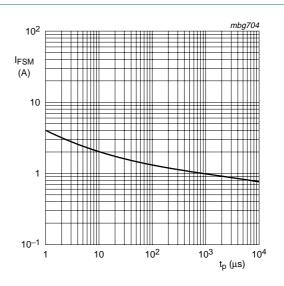
- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 85 \, ^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$
- (4) $T_{amb} = -40 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 85 \, ^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$
- (4) $T_{amb} = -40 \, ^{\circ}C$

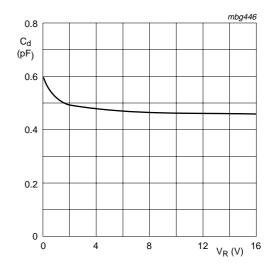
Fig 3. Reverse current as a function of reverse voltage; typical values



Based on square wave currents.

 $T_j = 25$ °C; prior to surge

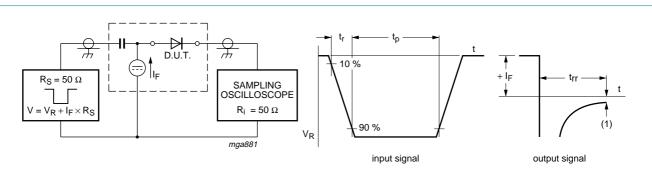
Fig 2. Non-repetitive peak forward current as a function of pulse duration; maximum values



 $f = 1 \text{ MHz}; T_{amb} = 25 \, ^{\circ}\text{C}$

Fig 4. Diode capacitance as a function of reverse voltage; typical values

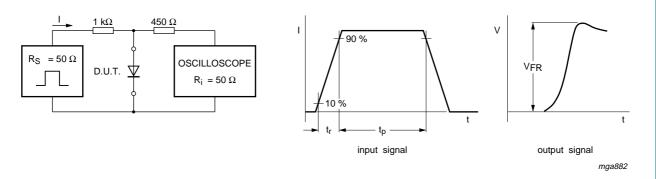
8. Test information



(1) $I_R = 1 \text{ mA}$

Input signal: reverse pulse rise time t_r = 0.6 ns; reverse voltage pulse duration t_p = 100 ns; duty cycle δ = 0.05 Oscilloscope: rise time t_r = 0.35 ns

Fig 5. Reverse recovery time test circuit and waveforms

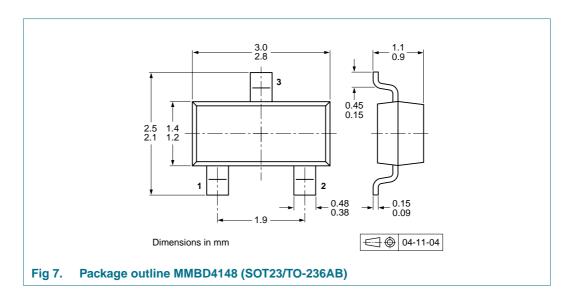


Input signal: forward pulse rise time t_r = 20 ns; forward current pulse duration $t_p \ge 100$ ns; duty cycle $\delta \le 0.005$

Fig 6. Forward recovery voltage test circuit and waveforms

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9. Package outline



10. Packing information

Table 8. Packing methods

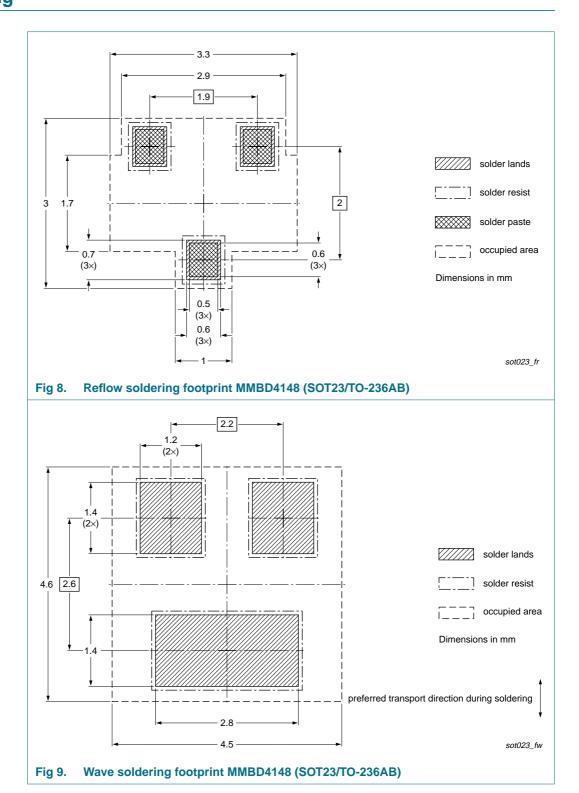
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
MMBD4148	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

[1] For further information and the availability of packing methods, see Section 14.

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11. Soldering



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12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
MMBD4148_1	20090604	Product data sheet	-	-

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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